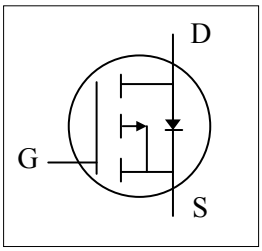
AP4P040J

Halogen-Free Product

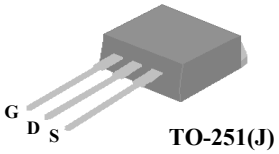
Advanced Power Electronics Corp.

P-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ **Lower Gate Charge**
- ▼ **Simple Drive Requirement**
- ▼ **Fast Switching Characteristic**
- ▼ **RoHS Compliant & Halogen-Free**



BV_{DSS}	-40V
$R_{DS(ON)}$	40mΩ
I_D	-19.6A



TO-251(J)

Description

AP4P040 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The straight lead version TO-251 package is widely preferred for all commercial-industrial through hole applications.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V	-19.6	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V	-12.4	A
I_{DM}	Pulsed Drain Current[1]	-80	A
P_D@T_C=25℃	Total Power Dissipation	25	W
P_D@T_A=25℃	Total Power Dissipation[4]	1.13	W
E_{AS}	Single Pulse Avalanche Energy[3]	16.2	mJ
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance Junction-case	5	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-40	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V, I_D=-10A	-	-	40	mΩ
		V_{GS}=-4.5V, I_D=-6A	-	-	60	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1	-	-3	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-10A	-	17	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-32V, V_{GS}=0V	-	-	-1	uA
I_{GSS}	Gate-Source Leakage	V_{GS}= ±20V, V_{DS}=0V	-	-	±0.1	uA
Q_g	Total Gate Charge	I_D=-6A	-	12	19.2	nC
Q_{gs}	Gate-Source Charge	V_{DS}=-32V	-	4.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=-4.5V	-	4.5	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=-20V	-	10	-	ns
t_r	Rise Time	I_D=-10A	-	26	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	37	-	ns
t_f	Fall Time	V_{GS}=-10V	-	38	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1340	2144	pF
C_{oss}	Output Capacitance	V_{DS}=-20V	-	120	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	80	-	pF
R_g	Gate Resistance	f=1.0MHz	-	8.5	17	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=-10A, V_{GS}=0V	-	-	-1.2	V
t_{rr}	Reverse Recovery Time	I_S=-10A, V_{GS}=0V,	-	12	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	6	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Starting T_j=25°C , V_{DD}=-30V , L=0.1mH , R_G=25Ω, V_{GS}=-10V

4.Surface mounted on 1 in^2 copper pad of FR4 board

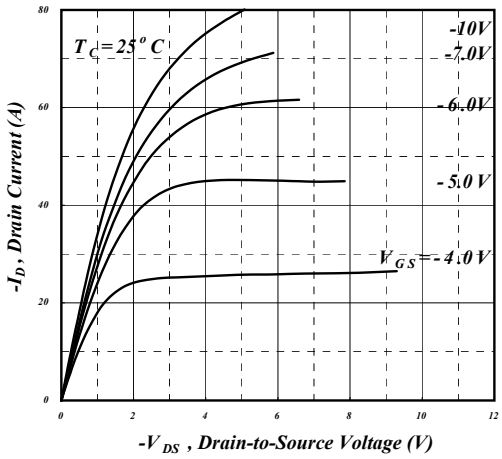


Fig 1. Typical Output Characteristics

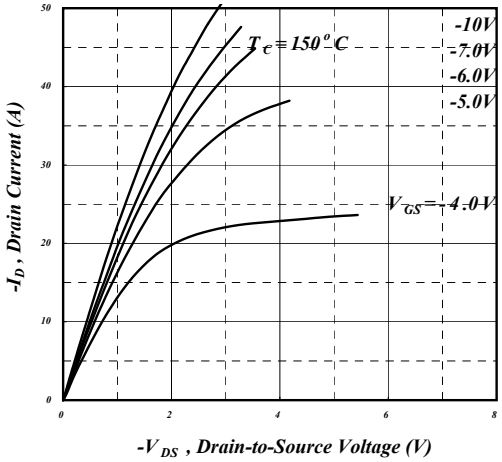


Fig 2. Typical Output Characteristics

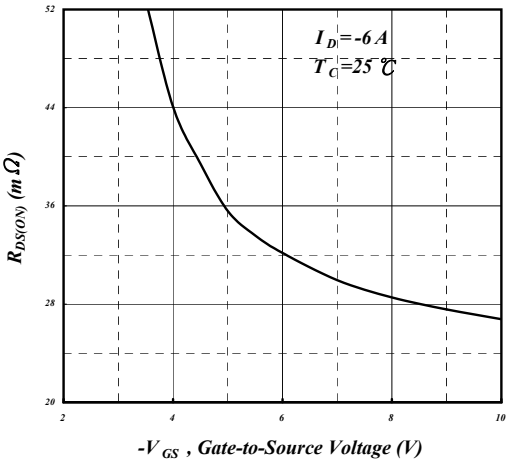


Fig 3. On-Resistance v.s. Gate Voltage

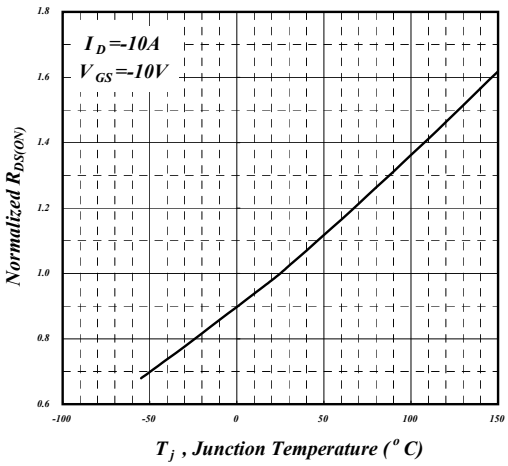


Fig 4. Normalized On-Resistance v.s. Junction Temperature

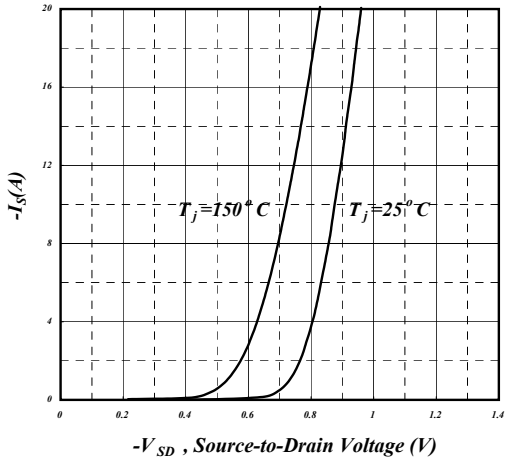


Fig 5. Forward Characteristic of Reverse Diode

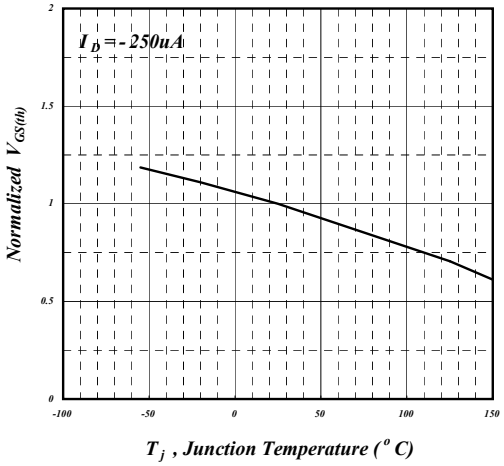


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

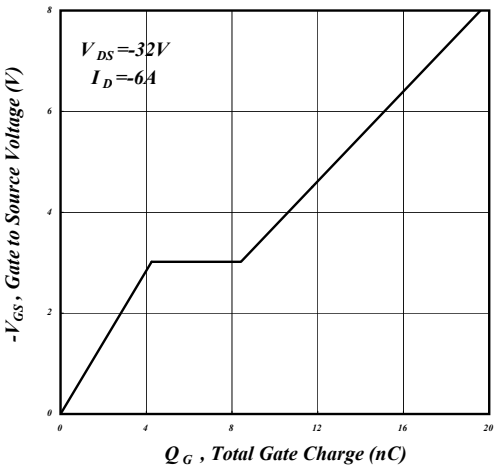


Fig 7. Gate Charge Characteristics

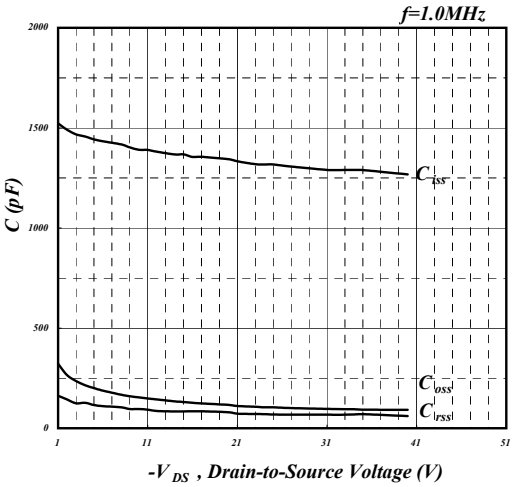


Fig 8. Typical Capacitance Characteristics

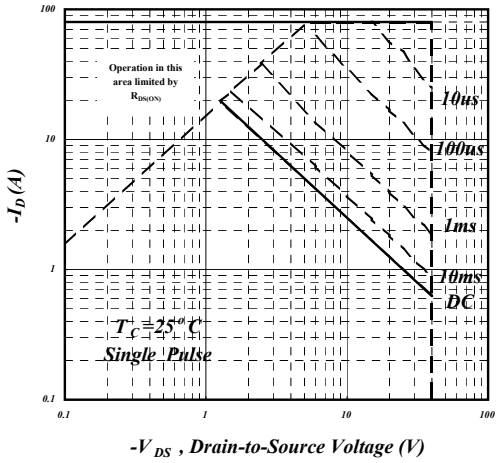


Fig 9. Maximum Safe Operating Area

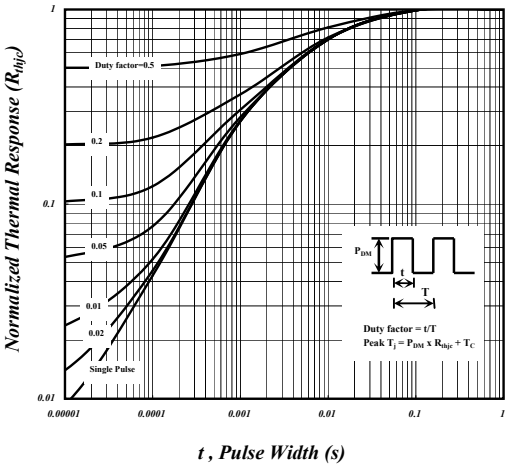


Fig 10. Effective Transient Thermal Impedance

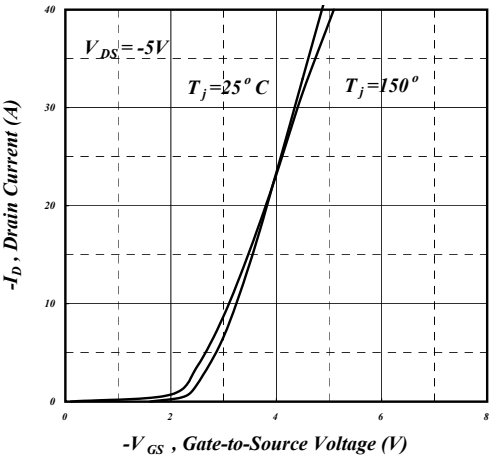


Fig 11. Transfer Characteristics

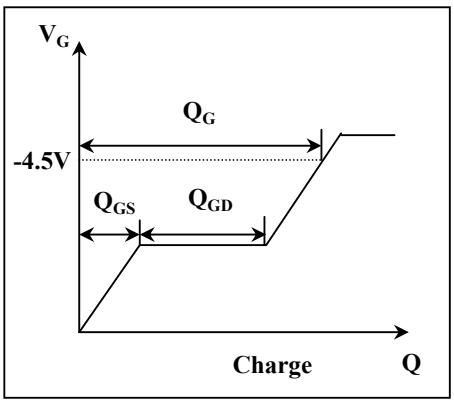


Fig 12. Gate Charge Waveform

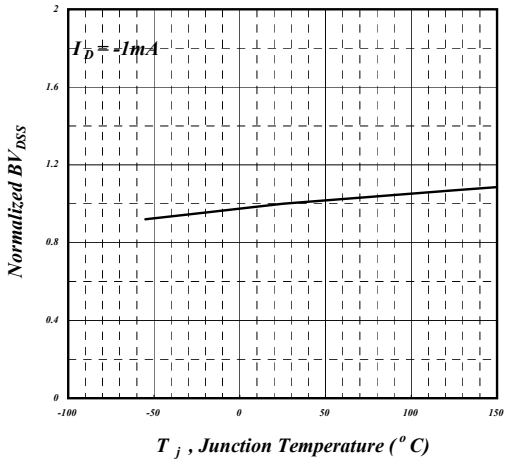


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

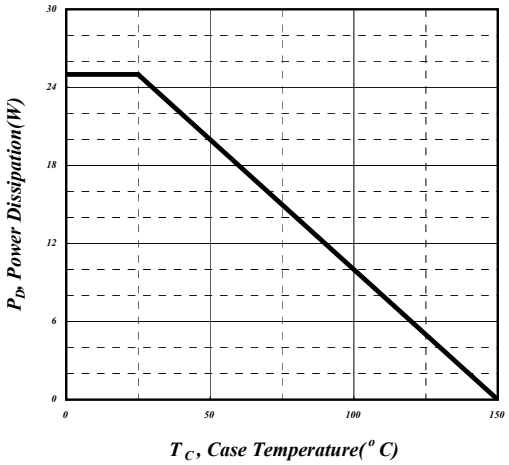


Fig 14. Total Power Dissipation

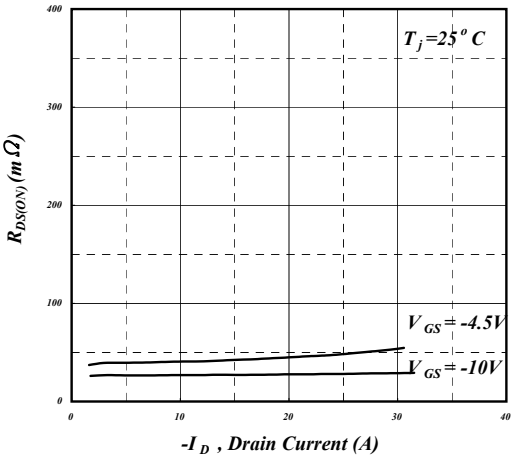


Fig 15. Typ. Drain-Source on State Resistance

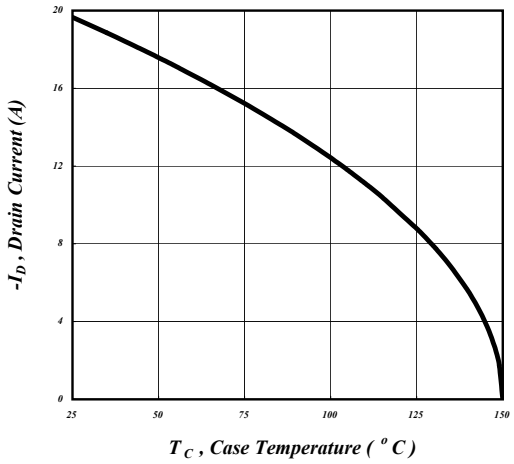


Fig 16. Drain Current v.s. Case Temperature

MARKING INFORMATION